

FEATURES

Low offset voltage: 100 μV maximum at $V_S = 5\text{ V}$

Low input bias current: 1 pA maximum

Single-supply operation: 5 V to 16 V

Low noise: 10 nV/ $\sqrt{\text{Hz}}$

Wide bandwidth: 4 MHz

Unity-gain stable

Small package options

3 mm \times 3 mm 8-lead LFCSP

8-lead MSOP and narrow SOIC

14-lead TSSOP and narrow SOIC

APPLICATIONS

Sensors

Medical equipment

Consumer audio

Photodiode amplification

ADC drivers

GENERAL DESCRIPTION

The AD8661/AD8662/AD8664¹ are rail-to-rail output, single-supply amplifiers that use the Analog Devices, Inc., patented DigiTrim[®] trimming technique to achieve low offset voltage.

The AD8661/AD8662/AD8664 series features extended operating ranges, with supply voltages up to 16 V. It also features low input bias current, wide signal bandwidth, and low input voltage and current noise.

The combination of low offset, very low input bias current, and a wide supply range makes these amplifiers useful in a wide variety of applications usually associated with higher priced JFET amplifiers. Systems using high impedance sensors, such as photodiodes, benefit from the combination of low input bias current, low noise, low offset, and wide bandwidth. The wide operating voltage range meets the demands of high performance analog-to-digital converters (ADCs) and digital-to-analog

¹ Protected by U.S. Patents 6,194,962 and 6,696,894.

Rev. E

[Document Feedback](#)

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

PIN CONFIGURATIONS

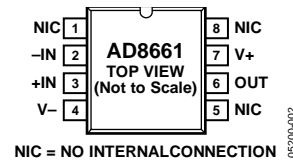
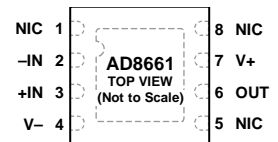


Figure 1. AD8661, 8-Lead SOIC (R-8)



NOTES
1. NIC = NO INTERNAL CONNECTION.
2. CONNECT THE EXPOSED PAD TO V₋.

Figure 2. AD8661, 8-Lead LFCSP (CP-8-13)

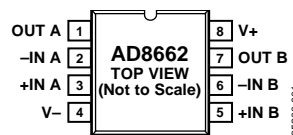


Figure 3. AD8662, 8-Lead SOIC (R-8)

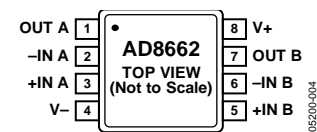


Figure 4. AD8662, 8-Lead MSOP (RM-8)

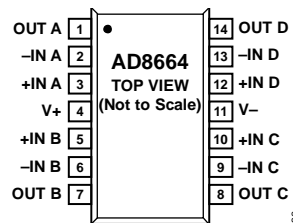


Figure 5. AD8664, 14-Lead SOIC (R-14)

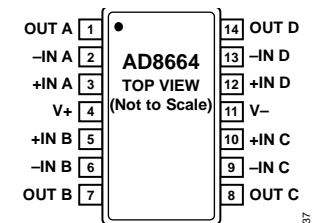


Figure 6. AD8664, 14-Lead TSSOP (RU-14)

converters (DACs). Audio applications and medical monitoring equipment can take advantage of the high input impedance, low voltage, low current noise, and wide bandwidth.

The single AD8661 is available in a narrow 8-lead SOIC package and a very thin, dual lead, 8-lead LFCSP. The AD8661 SOIC package is specified over the extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The AD8661 LFCSP is specified over the industrial temperature range of -40°C to $+85^{\circ}\text{C}$. The AD8662 is available in a narrow 8-lead SOIC package and an 8-lead MSOP, both specified over the extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The AD8664 is available in a narrow 14-lead SOIC package and a 14-lead TSSOP, both with an extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$.

SPECIFICATIONS

AD8661/AD8662/AD8664 ELECTRICAL CHARACTERISTICS—SOIC, MSOP, AND TSSOP

$V_S = 5.0\text{ V}$, $V_{CM} = V_S/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = V_S/2$		30	100	μV
AD8661		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			1000	μV
AD8661		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1400	μV
AD8662		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1000	μV
AD8664		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1200	μV
Input Bias Current	I_B			0.3	1	pA
		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			50	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			300	pA
Input Offset Current	I_{OS}			0.2	0.5	pA
		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			20	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			75	pA
Input Voltage Range			-0.1		+3.0	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+3.0\text{ V}$	85	100		dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		80	100	
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }4.5\text{ V}$	100	220		V/mV
Offset Voltage Drift	TCV_{OS}					
AD8661		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	10	$\mu\text{V}/^\circ\text{C}$
AD8662, AD8664		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	9	$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1\text{ mA}$	4.85	4.93		V
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	4.80			V
Output Voltage Low	V_{OL}	$I_L = 1\text{ mA}$		50	100	mV
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			110	mV
Short-Circuit Current	I_{SC}			± 19		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 1\text{ MHz}$, $A_V = 1$		50		Ω
POWER SUPPLY						
Supply Current per Amplifier	I_{SY}	$V_O = V_S/2$		1.15	1.40	mA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			2.0	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_O			65		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	e_n p-p	$f = 0.1\text{ Hz to }10\text{ Hz}$		2.5		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		12		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$		10		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		0.1		$\text{pA}/\sqrt{\text{Hz}}$

AD8661/AD8662/AD8664 ELECTRICAL CHARACTERISTICS—SOIC, MSOP, AND TSSOP

$V_S = 16.0\text{ V}$, $V_{CM} = V_S/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = V_S/2$		50	160	μV
AD8661		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			1000	μV
AD8661		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1400	μV
AD8662		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1000	μV
AD8664		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			1200	μV
Input Bias Current	I_B			0.3	1	pA
		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			50	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			300	pA
Input Offset Current	I_{OS}			0.2	0.5	pA
		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$			20	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			75	pA
Input Voltage Range			-0.1		+14.0	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+14.0\text{ V}$	90	110		dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	90	110		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }15.5\text{ V}$	200	360		V/mV
Offset Voltage Drift	TCV_{OS}					
AD8661		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	10	$\mu\text{V}/^\circ\text{C}$
AD8662, AD8664		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	9	$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1\text{ mA}$	15.93	15.97		V
		$I_L = 10\text{ mA}$	15.60	15.70		V
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	15.50			V
Output Voltage Low	V_{OL}	$I_L = 1\text{ mA}$		24	50	mV
		$I_L = 10\text{ mA}$		190	300	mV
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			350	mV
Short-Circuit Current	I_{SC}			± 140		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 1\text{ MHz}$, $A_V = 1$		45		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 5\text{ V to }16\text{ V}$	95	110		dB
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	95	115		dB
Supply Current per Amplifier	I_{SY}	$V_O = V_S/2$		1.25	1.55	mA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			2.1	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_O			65		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	$e_n\text{ p-p}$	$f = 0.1\text{ Hz to }10\text{ Hz}$		2.5		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		12		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$		10		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		0.1		$\text{pA}/\sqrt{\text{Hz}}$

AD8661 ELECTRICAL CHARACTERISTICS—LFCSP ONLY

$V_S = 5.0\text{ V}$, $V_{CM} = V_S/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 3.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = V_S/2$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		50	300	μV
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		0.3	1	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		0.2	0.5	pA
Input Voltage Range		$-40^\circ\text{C} < T_A < +85^\circ\text{C}$	-0.1		20	pA
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+3.0\text{ V}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	85	100	+3.0	V
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }4.5\text{ V}$	80	100		dB
Offset Voltage Drift	TCV_{OS}	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$	100	240		V/mV
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	4.85	4.93		V
Output Voltage Low	V_{OL}	$I_L = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	4.80	50	100	V
Short-Circuit Current	I_{SC}				120	mV
Closed-Loop Output Impedance	Z_{OUT}	$f = 1\text{ MHz}$, $A_V = 1$		± 19		mA
POWER SUPPLY						
Supply Current per Amplifier	I_{SY}	$V_O = V_S/2$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		1.15	1.40	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_O			65		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	$e_n\text{ p-p}$	$f = 0.1\text{ Hz to }10\text{ Hz}$		2.5		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$		12		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$		10		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		0.1		$\text{pA}/\sqrt{\text{Hz}}$

AD8661 ELECTRICAL CHARACTERISTICS—LFCSP ONLY

$V_S = 16.0\text{ V}$, $V_{CM} = V_S/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = V_S/2$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		50	300	μV
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		0.3	1	μA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		0.2	0.5	μA
Input Voltage Range			-0.1		+14.0	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+14.0\text{ V}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	90	110		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }15.5\text{ V}$	200	420		V/mV
Offset Voltage Drift	TCV_{OS}	$-40^\circ\text{C} < T_A < +85^\circ\text{C}$		4	17	$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1\text{ mA}$ $I_L = 10\text{ mA}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	15.95 15.60 15.50	15.97 15.70		V V V
Output Voltage Low	V_{OL}	$I_L = 1\text{ mA}$ $I_L = 10\text{ mA}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		24 210	50 350	mV mV mV
Short-Circuit Current	I_{SC}			± 140		mA
Closed-Loop Output Impedance	Z_{OUT}	$f = 1\text{ MHz}$, $A_V = 1$		45		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 5\text{ V to }16\text{ V}$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$	95 95	110 115		dB dB
Supply Current per Amplifier	I_{SY}	$V_O = V_S/2$ $-40^\circ\text{C} < T_A < +85^\circ\text{C}$		1.25	1.55 1.9	mA mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		V/ μs
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_O			65		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	$e_n\text{ p-p}$	$f = 0.1\text{ Hz to }10\text{ Hz}$		2.5		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$ $f = 10\text{ kHz}$		12 10		nV/ $\sqrt{\text{Hz}}$ nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1\text{ kHz}$		0.1		pA/ $\sqrt{\text{Hz}}$

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
Supply Voltage	18V
Input Voltage	-0.1 V to V_S
Differential Input Voltage	18V
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-60°C to +150°C
Operating Temperature Range	
R-8, RM-8, R-14, and RU-14	-40°C to +125°C
CP-8-13	-40°C to +85°C
Junction Temperature Range	-65°C to +150°C
Lead Temperature, Soldering (60 sec)	300°C

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 6. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead SOIC	121	43	°C/W
8-Lead LFCSP	75 ¹	18 ¹	°C/W
8-Lead MSOP	142	44	°C/W
14-Lead SOIC	88.2	56.3	°C/W
14-Lead TSSOP	114	23.3	°C/W

¹ Exposed pad soldered to application board.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

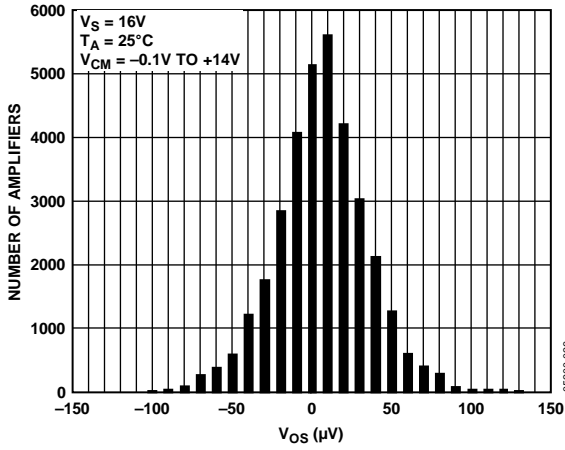


Figure 7. Input Offset Voltage Distribution

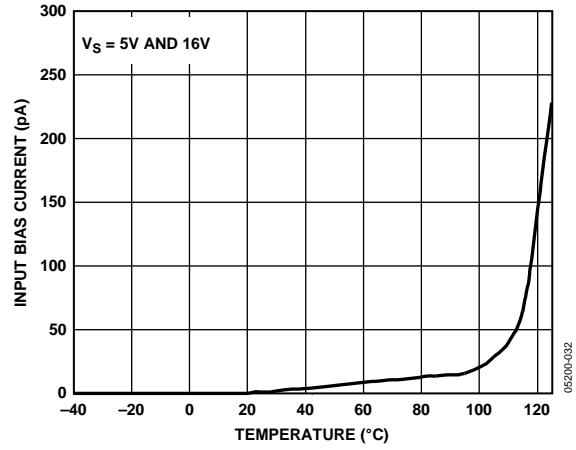


Figure 10. Input Bias Current vs. Temperature

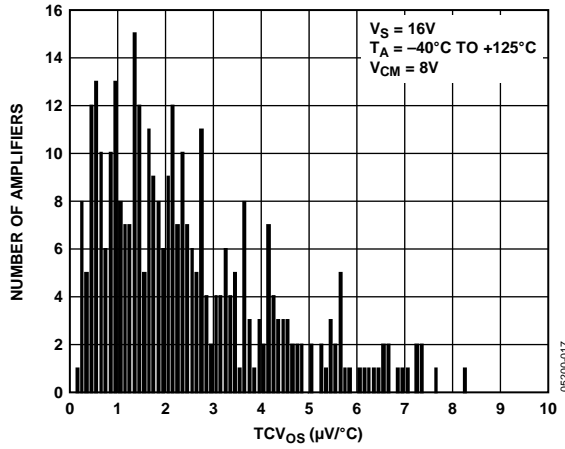


Figure 8. Offset Voltage Drift Distribution

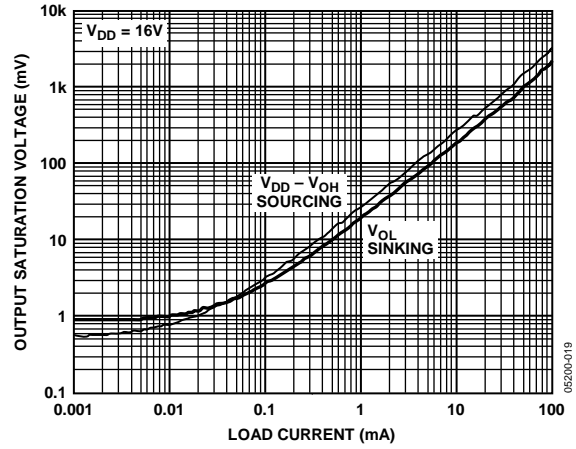


Figure 11. Output Swing Saturation Voltage vs. Load Current

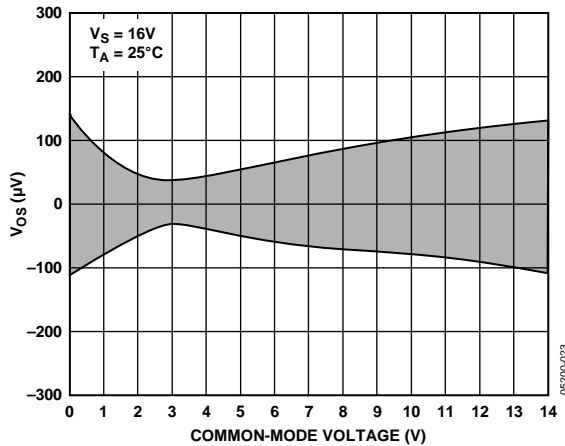


Figure 9. Input Offset Voltage vs. Common-Mode Voltage

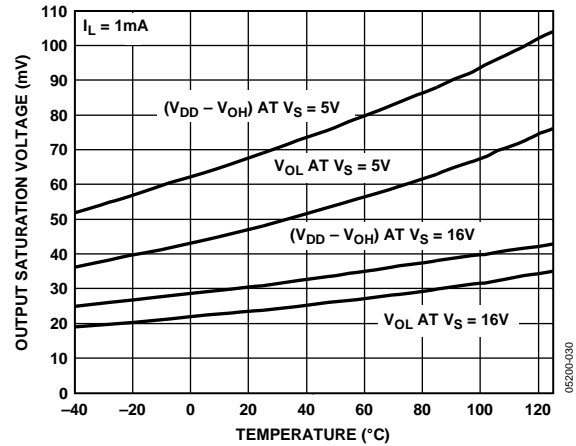


Figure 12. Output Swing Saturation Voltage vs. Temperature, $I_L = 1 \text{ mA}$

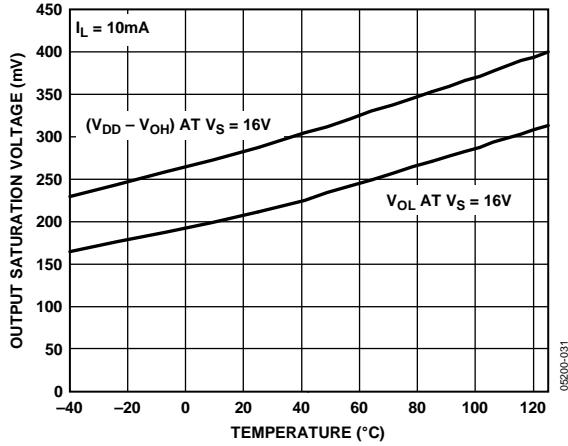


Figure 13. Output Swing Saturation Voltage vs. Temperature, $I_L = 10\text{ mA}$

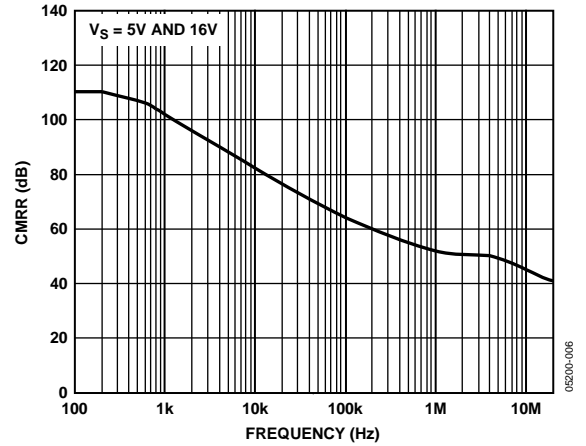


Figure 16. CMRR vs. Frequency



Figure 14. Open-Loop Gain and Phase Shift vs. Frequency



Figure 17. PSRR vs. Frequency

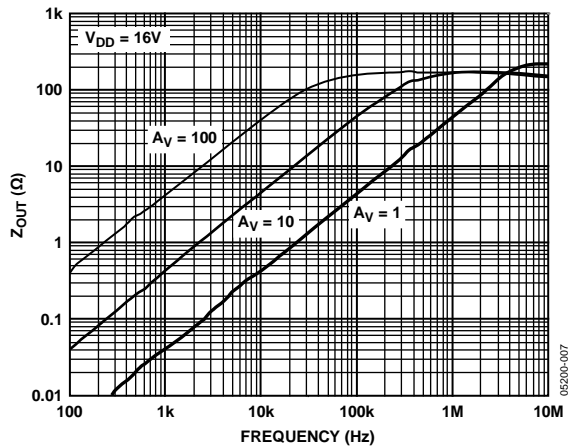


Figure 15. Closed-Loop Output Impedance vs. Frequency



Figure 18. Small Signal Overshoot vs. Load Capacitance



Figure 19. Supply Current vs. Temperature



Figure 22. Small Signal Transient Response



Figure 20. Supply Current vs. Supply Voltage (Dual-Supply Configuration), $T_A = 25^\circ\text{C}$

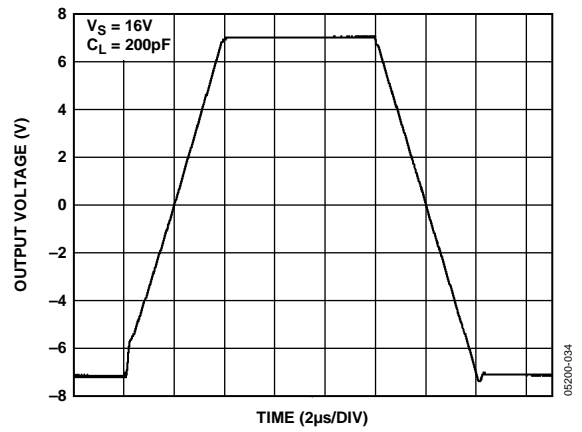


Figure 23. Large Signal Transient Response



Figure 21. 0.1 Hz to 10 Hz Input Voltage Noise



Figure 24. Positive Overload Recovery



Figure 25. Negative Overload Recovery

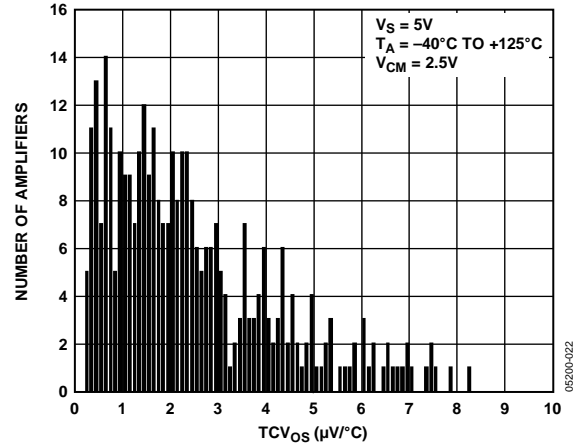


Figure 28. Offset Voltage Drift Distribution

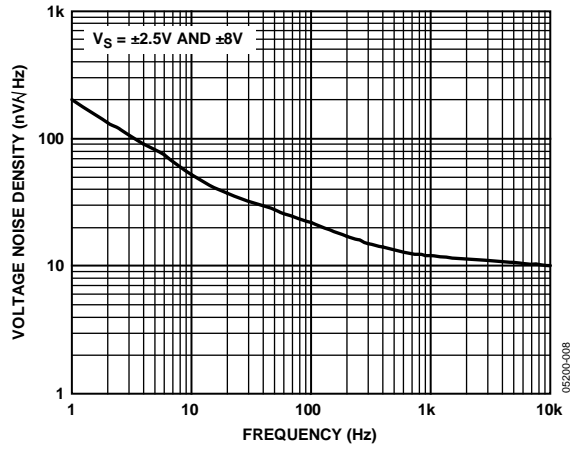


Figure 26. Voltage Noise Density vs. Frequency

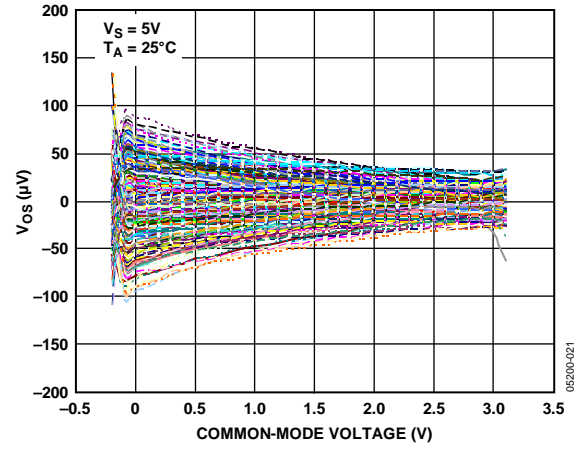


Figure 29. Input Offset Voltage vs. Common-Mode Voltage



Figure 27. Input Offset Voltage Distribution

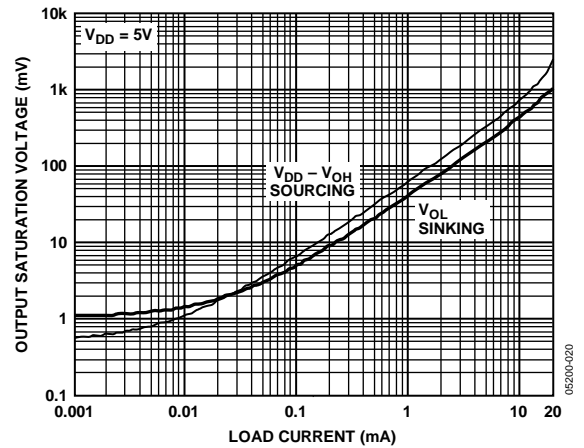


Figure 30. Output Swing Saturation Voltage vs. Load Current



Figure 31. Closed-Loop Output Impedance vs. Frequency

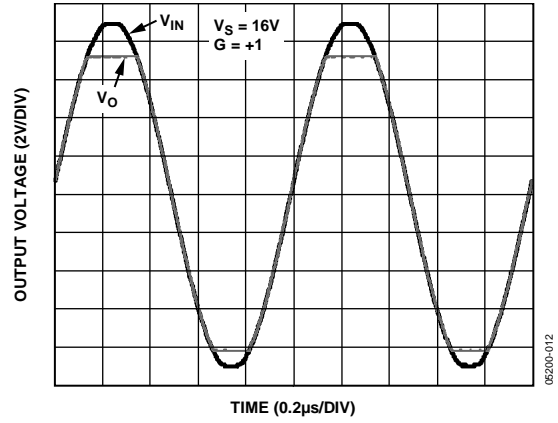
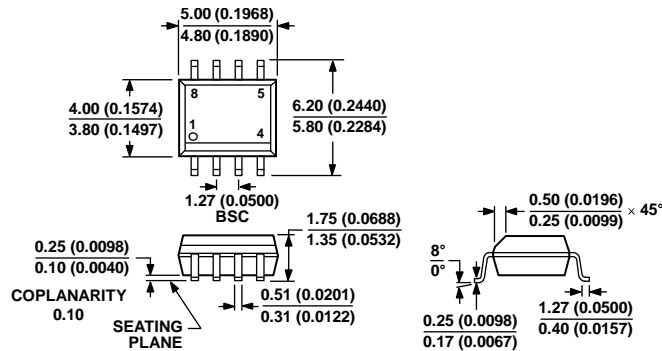


Figure 33. No Phase Reversal



Figure 32. Large Signal Transient Response

OUTLINE DIMENSIONS

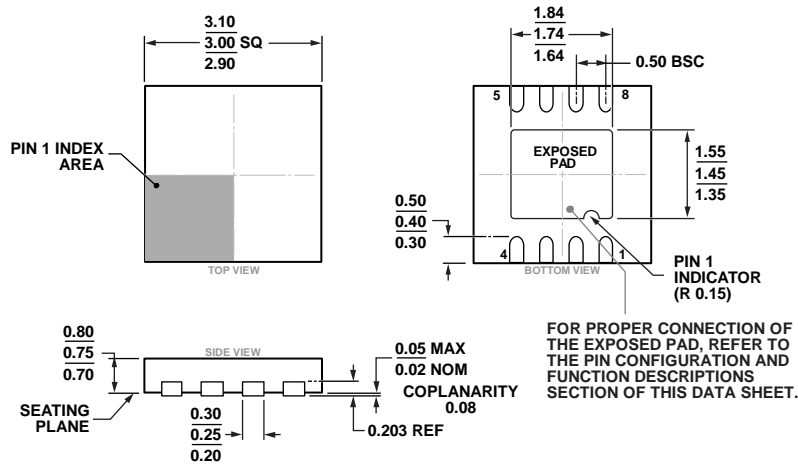


COMPLIANT TO JEDEC STANDARDS MS-012-A
 CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
 (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
 REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

060506-A

Figure 34. 8-Lead Small Outline Package [SOIC_N]
 Narrow Body
 (R-8)

Dimensions shown in millimeters and (inches)

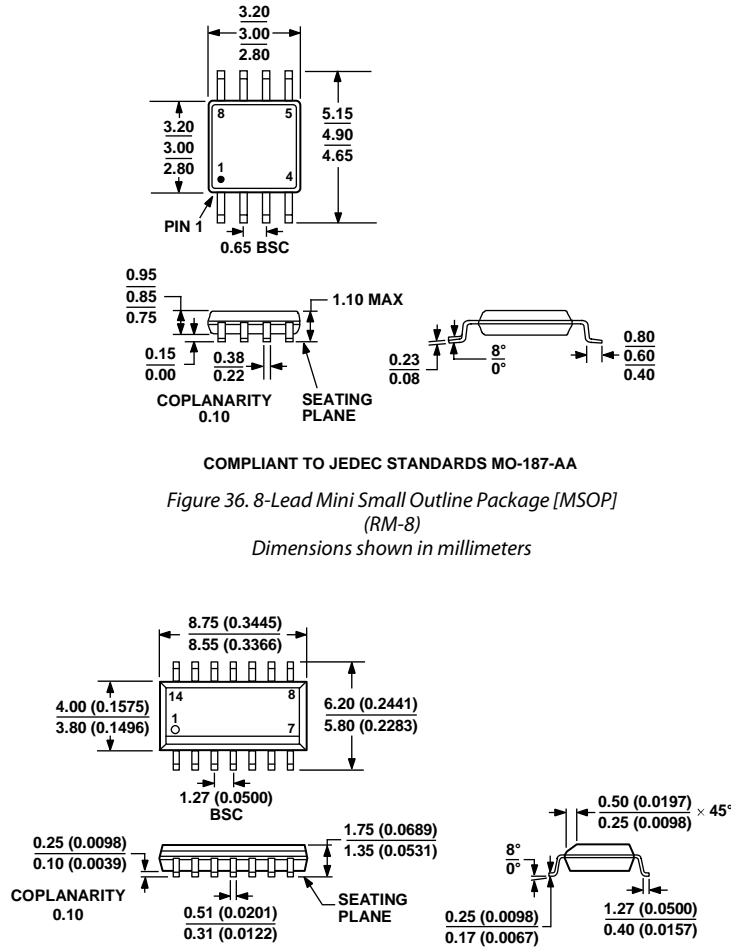


COMPLIANT TO JEDEC STANDARDS MO-229-WEED-4

Figure 35. 8-Lead Lead Frame Chip Scale Package [LFCSP]
 3 mm x 3 mm Body and 0.75 mm Package Height
 (CP-8-13)

Dimensions shown in millimeters

05-11-2016-A



COMPLIANT TO JEDEC STANDARDS MO-187-AA

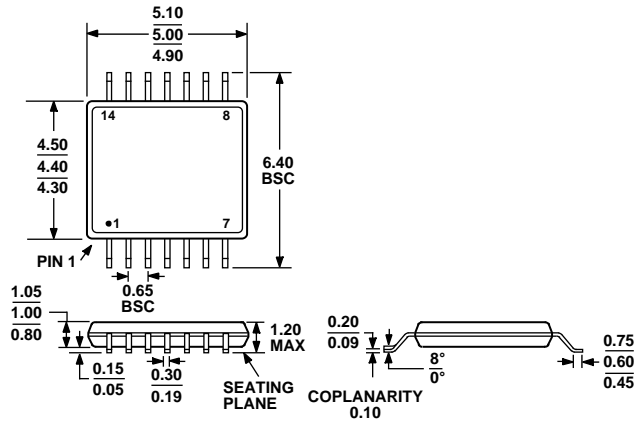
Figure 36. 8-Lead Mini Small Outline Package [MSOP] (RM-8)

Dimensions shown in millimeters

COMPLIANT TO JEDEC STANDARDS MS-012-AB
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 37. 14-Lead Standard Small Outline Package [SOIC_N] Narrow Body (R-14)

Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-153-AB-1

Figure 38. 14-Lead Thin Shrink Small Outline Package [TSSOP] (RU-14)

Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	Branding
AD8661ARZ	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8661ARZ-REEL	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8661ARZ-REEL7	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8661ACPZ-R2	−40°C to +85°C	8-Lead Lead Frame Chip Scale Package [LFCSP]	CP-8-13	AOM
AD8661ACPZ-REEL7	−40°C to +85°C	8-Lead Lead Frame Chip Scale Package [LFCSP]	CP-8-13	AOM
AD8662ARZ	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8662ARZ-REEL	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8662ARZ-REEL7	−40°C to +125°C	8-Lead Small Outline Package [SOIC_N]	R-8	
AD8662ARMZ	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A10
AD8662ARMZ-REEL	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A10
AD8664ARZ	−40°C to +125°C	14-Lead Standard Small Outline Package [SOIC_N]	R-14	
AD8664ARZ-REEL	−40°C to +125°C	14-Lead Standard Small Outline Package [SOIC_N]	R-14	
AD8664ARZ-REEL7	−40°C to +125°C	14-Lead Standard Small Outline Package [SOIC_N]	R-14	
AD8664ARUZ	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	
AD8664ARUZ-REEL	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	

¹ Z = RoHS Compliant Part.

NOTES



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.